CNZ1021, CNZ1022, CNZ1023, CNA1009H (ON1021, ON1022, ON1023, ON1024)

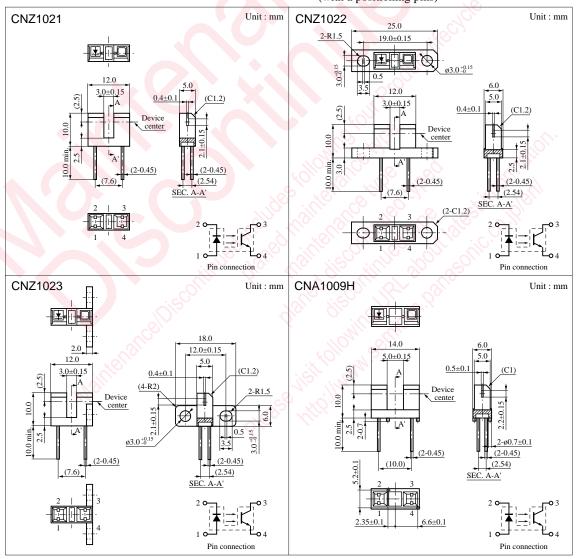
Photo Interrupters

Overview

CNZ1021 series is a transmissive photosensor series in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

Features

- Position detection accuracy: 0.25 mm
- Gap width: 3 mm (CNZ1021, CNZ1022, CNZ1023)
 5 mm (CNA1009H)



(Note) 1. Tolerance unless otherwise specified is ± 0.3 . 2. () Dimension is reference.

Note) The part numbers in the parenthesis show conventional part number.

■ Absolute Maximum Ratings (Ta = 25°C)

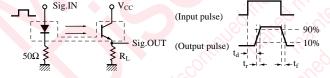
F	Parameter	Symbol	Ratings	Unit
I (I'll	Reverse voltage (DC)	V_R	5	V
Input (Light emitting diode)	Forward current (DC)	I_F	50	mA
	Power dissipation	P_D^{*1}	75	mW
	Collector current	I_{C}	20	mA
Output (Photo	Collector to emitter voltage	V_{CEO}	30	V
transistor)	Emitter to collector voltage	V_{ECO}	5	V
	Collector power dissipation	P _C *2	100	mW
Tomporoturo	Operating ambient temperature	Topr	-25 to +85	°C
Temperature	Storage temperature	T _{stg}	-40 to +100	°C

^{*1} Input power derating ratio is 1.0 mW/°C at Ta \geq 25°C.

■ Electrical Characteristics (Ta = 25°C)

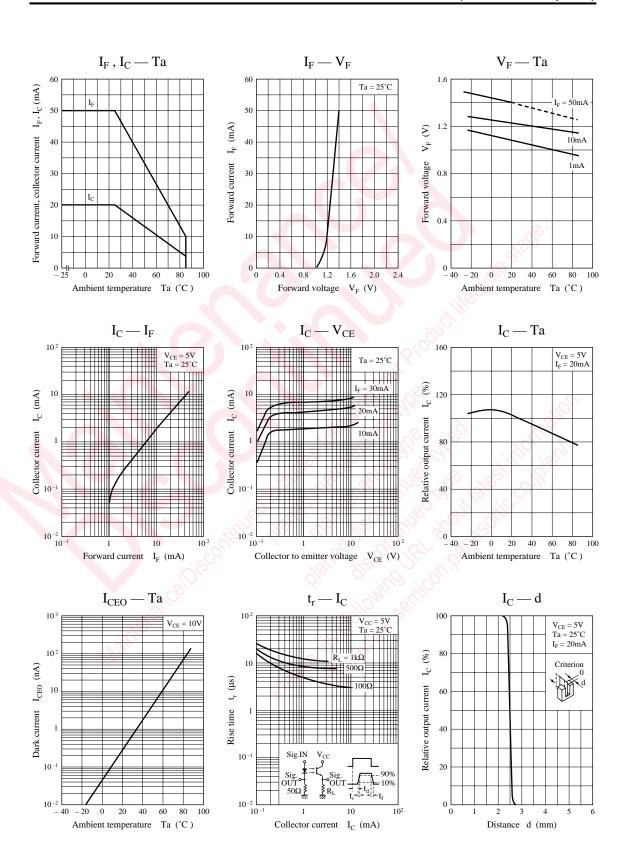
	Parameter	Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	,	$I_F = 20 \text{mA}$,	1.25	1.4	V
	Reverse current (DC)	I _R	$V_R = 3V$			10	μΑ
Output characteristics	Collector cutoff current	I_{CEO}	$V_{CE} = 10V$		10	200	nA
Transfer characteristics	Collector current	I_{C}	$V_{CC} = 5V$, $I_F = 20mA$, $R_L = 100\Omega$	0.5		15	mA
	Collector to emitter saturation voltage	V _{CE(sat)}	$I_F = 40 \text{mA}, I_C = 1 \text{mA}$	60		0.4	V
	Response time	t_r, t_f^*	$V_{CC} = 5V, I_C = 1mA, R_L = 100\Omega$	7.60	5	10,	μs

^{*} Switching time measurement circuit



- t_d: Delay time
- t_r: Rise time (Time required for the collector current to increase from 10% to 90% of its final value)
- t_f: Fall time (Time required for the collector current to decrease from 90% to 10% of its initial value)

^{*2} Output power derating ratio is 1.33 mW/°C at Ta ≥ 25°C.





■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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